

N-channel LFPAK 40 V 3.3 mΩ standard level MOSFET Rev. 04 — 25 October 2010 Product da

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC convertors
- Lithium-ion battery protection
- Load switching

1.4 Quick reference data

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	4.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	2.6	3.3	mΩ



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Table 1. Quick reference datacontinued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A};$	-	11.2	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 20 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	49	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	162	mJ

2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

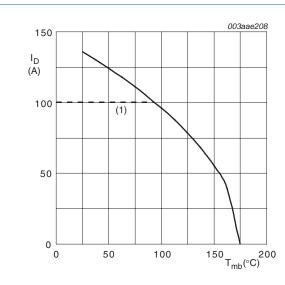
Table 3.	Ordering in	formation		
Type numb	er	Package		
		Name	Description	Version
PSMN3R3-4	40YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	40	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	97	А
	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	100	А	
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	546	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	117	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	n diode				
I _S	source current	T _{mb} = 25 °C	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	546	А
Avalanche ru	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 40$ V; unclamped; R_{GS} = 50 Ω	-	162	mJ



 $V_{\rm GS}$ \geq 10 V; (1) Capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature

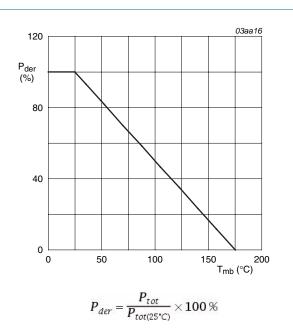
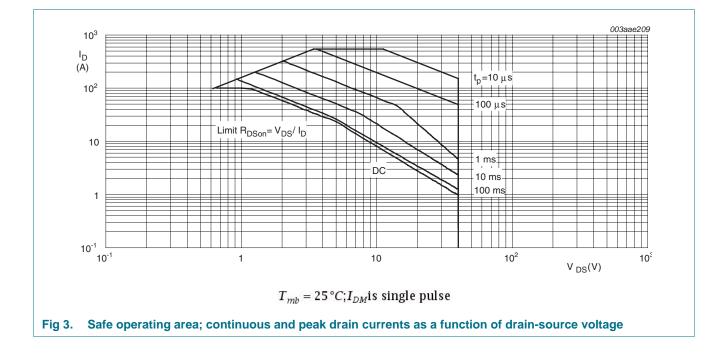


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN3R3-40YS

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5. Thermal characteristics

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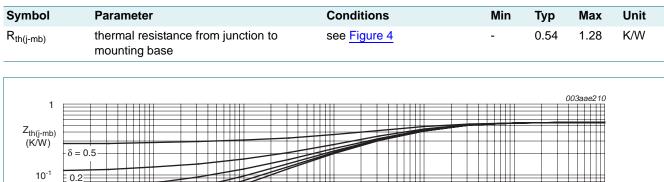
0.05[.] 0.02

single shot

10⁻²

10⁻³

Fig



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Table 5. Thermal characteristics

	10 ⁻⁶	10 ⁻⁵	10 ⁻⁴	10 ⁻³	10 ⁻²	10 ⁻¹	t _p (s)	1
j 4 .	Transient therr	nal impedance f	rom junction to	mounting base a	as a function of	pulse d	uration; t	ypical

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	36	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V	
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 125 °C	-	10	100	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^\circ\text{C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	4.5	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see Figure 12	-	4.7	5.94	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	2.6	3.3	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.67	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	39	-	nC	
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	49	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	13.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u>	-	8.3	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.5	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11.2	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2754	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	600	-	pF
C _{rss}	reverse transfer capacitance		-	316	-	pF
d(on)	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	21	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	38	-	ns
t _f	fall time		-	14	-	ns

Symbol

Source-drain diode

PSMN3R3-40YS

Тур

Max

Unit

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Min

	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 17</u>	- 0.82 1.2 V
t _{rr}	reverse recovery time	$I_{S} = 40 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	- 44 - ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	- 48 - nC
100 I _D (A) 80	2010.8 6	3aae211 80 ID ID (A) 60 40 40	003aae212
40 20 0	V _{GS} (V	20	$T_{j} = 175 \circ C$ $T_{j} = 25 \circ C$
Fig 5.	0 0.25 0.5 0.75 $V_{\rm C}$ $T_{j}=25^{\circ}C$ Output characteristics: drain curr		2 4 $V_{GS}(V)$ 6 $V_{DS} > I_D \times R_{DSon}$
1	function of drain-source voltage;		characteristics: drain current as a of gate-source voltage; typical values
100 g _{fs} (S) 80 60	function of drain-source voltage;		<i>characteristics: drain current as a</i> of gate-source voltage; typical values
100 9 _{fs} (S) 80 60 40 20	function of drain-source voltage;	typical values function o Baae213 6000 C (pF) 4000 2000 0 0	003aae214
100 9 _{fs} (S) 80 60 40 20	function of drain-source voltage;	typical values function o Base213 6000 C (pF) 4000 2000	003aae214

Conditions

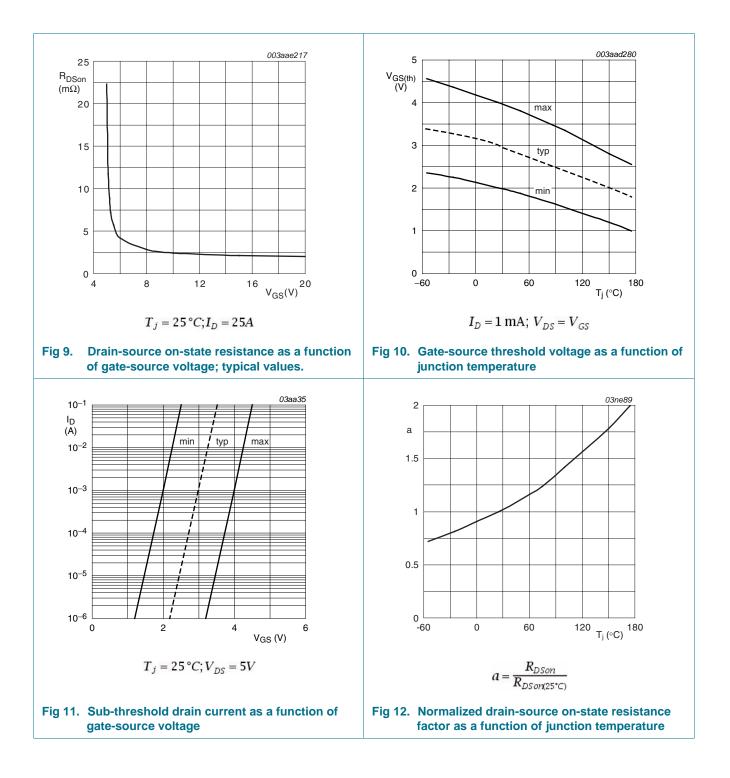
Table 6. Characteristics ... continued

Parameter

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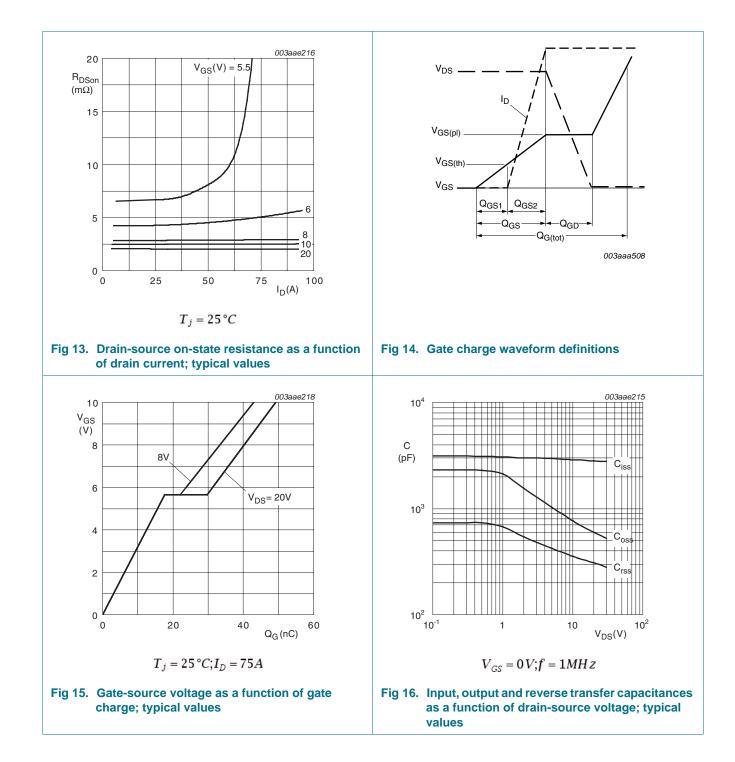
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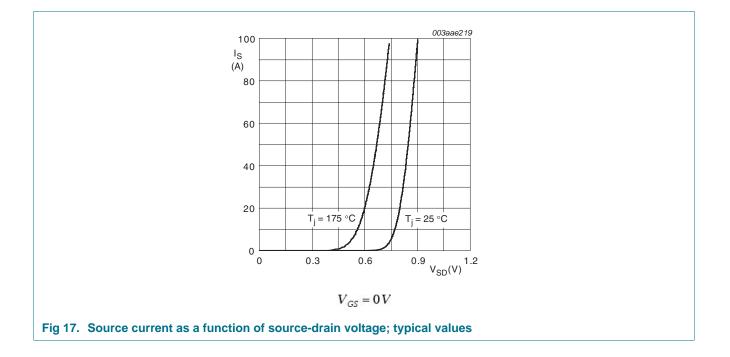
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7. Package outline

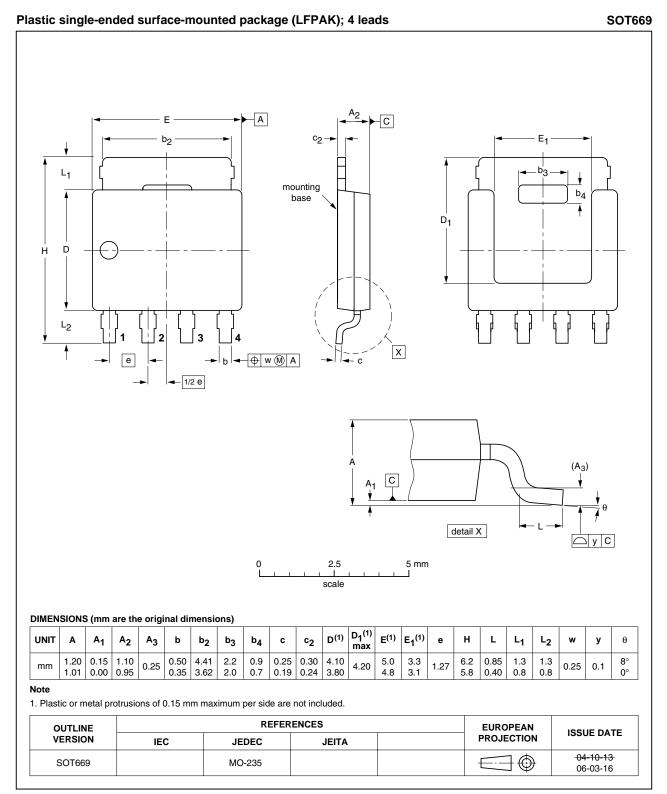


Fig 18. Package outline SOT669 (LFPAK)

PSMN3R3-40	YS	
Product	data	sheet

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-40YS v.4	20101025	Product data sheet	-	PSMN3R3-40YS v.3
Modifications:	 Various changes t 	o content.		
PSMN3R3-40YS v.3	20100930	Product data sheet	-	PSMN3R3-40YS v.2

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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